

IN THE CLAIMS

1. (Currently amended) A semiconductor device comprising:
a semiconductor substrate;
dummy patterns for a chemical mechanical polishing (CMP) method formed in a uniform pattern over the semiconductor substrate; and
marking patterns that are formed over the semiconductor substrate to correspond to predetermined groups of the dummy patterns,
wherein at least one dummy pattern is formed between two marking patterns,
wherein a number of the dummy patterns is substantially greater than a number of the marking patterns, wherein the marking patterns are smaller than the dummy patterns.

2. (Original) The semiconductor device of claim 1, wherein the marking patterns have a different shape from the dummy patterns.

3. (Original) The semiconductor device of claim 1, wherein the marking patterns have a different size from the dummy patterns.

4-22. (Canceled)

23. (Previously presented) A semiconductor device comprising:
a semiconductor substrate;
dummy patterns for a chemical mechanical polishing (CMP) method formed in a uniform pattern over the semiconductor substrate; and
marking patterns that are formed over the semiconductor substrate to correspond